

Supplementary materials to the paper:
Atomic layer deposition of HfS_2 from Tetrakis(dimethylamino)hafnium
Zsófia Baji*, Zsolt Fogarassy, Attila Sulyok, Péter Petrik
Centre for Energy Research, Institute of Technical Physics and Materials Science
Konkoly Thege M. út 29-33, 1121 Budapest, Hungary

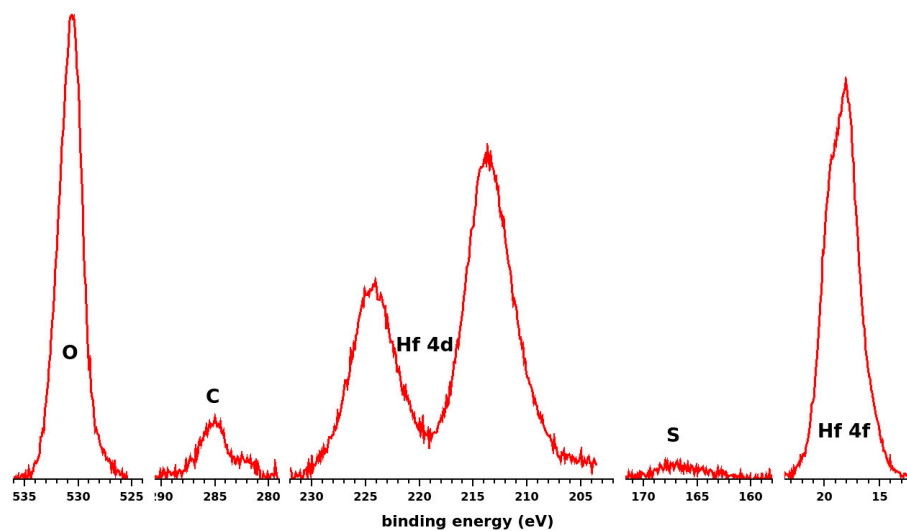


Figure S1. XPS spectrum observed on 400°C HfS_2 layer. It shows a low S content and partially oxidized state of Hf.

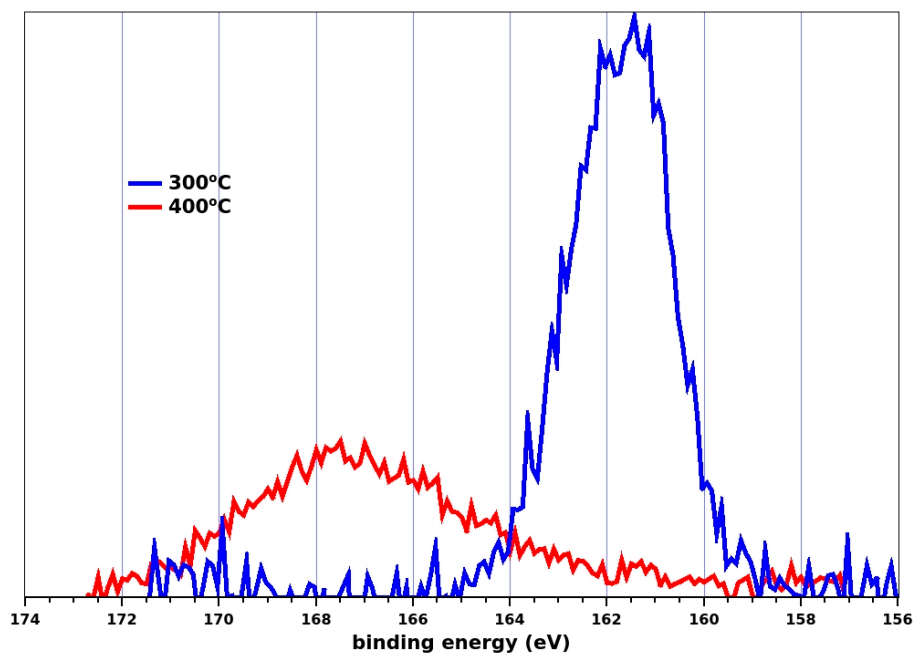


Figure S2. The alteration of sulfur chemical state is shown here by the S 2p peak. The change of binding energy clearly shows that the layer made at 300°C is in a well-defined sulfide state while the 400°C layer presents a mixture of differently oxidized sulfur compounds (SO_3 and SO_4) with smeared peak shape.